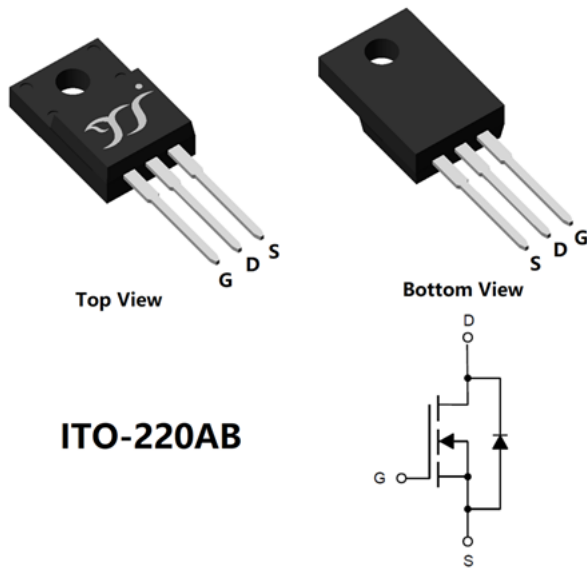


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 650V
- I_D 15A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<260m\Omega$
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Super Junction High Voltage MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Switching Mode Power Supplies (SMPS)
- PWM Motor Controls
- LED Lighting
- Adapter

Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V _{DS}	-	650	V
Gate-source Voltage			V _{GS}	-30	30	
Continuous Drain Current (Note 1,2)	Steady-State	T _A =25°C,V _{GS} =10V	I _D	-	1.7	A
		T _A =100°C,V _{GS} =10V		-	1.09	
Continuous Drain Current (Note 1,3)	Steady-State	T _C =25°C,V _{GS} =10V,Chip limitation		-	15	
		T _C =100°C,V _{GS} =10V		-	9.5	
Pulsed Drain Current	T _C =25°C,t _p ≤10μs			I _{DM}	-	
Maximum Body-Diode Continuous Current	T _C =25°C		I _S		15	
Maximum Body-Diode Pulsed Current	T _C =25°C,t _p ≤10μs		I _{SM}	-	45	
Avalanche Energy (non-repetitive)	T _J =25°C,V _G =10V,R _G =25Ω,L=30mH,I _{AS} =4.3A		EAS	-	277.35	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T _A =25°C	P _D	-	1.98	W
		T _A =100°C		-	0.79	
Total Power Dissipation (Note 1,3)	Steady-State	T _C =25°C		-	73	
		T _C =100°C		-	29	
MOSFET dv/dt Ruggedness	V _{DS} =0...325V, I _D <=14A,R _g =0Ω		dv/dt	-	46	V/ns
Reverse Diode dv/dt	V _{DS} =0...325V,I _D <=14A,di/dt=200A/us		dv/dt	-	8.3	
Maximum Diode Commutation Speed	V _{DS} =0...325V,I _D <=14A,R _g =0Ω		diff/dt	-	4197	A/us
Insulation withstand voltage	V _{rms} , t=60s		V _{ISO}	-	3.5	KV
Junction and Storage Temperature Range			T _J , T _{STG}	-55	150	°C

Thermal Resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	-	63	$^{\circ}C/W$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	1.7	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJF260C65BHJ	B1	YJF260C65BH	50	/	5000	Tube



YJF260C65BHJ

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA, T _j =25°C	650	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V, T _j =25°C	-	-	1	μA
		V _{DS} =650V, V _{GS} =0V, T _j =150°C	-	-	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V, T _j =25°C	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA, T _j =25°C	3.3	4.1	4.9	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7.5A, T _j =25°C	-	213	260	mΩ
		V _{GS} =10V, I _D =7.5A, T _j =150°C	-	543	663	
Diode Forward Voltage	V _{SD}	I _S =15A, V _{GS} =0V, T _j =25°C	-	0.88	1.2	V
Gate Resistance	R _G	f=1MHz, T _j =25°C	-	4.7	-	Ω
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =325V, V _{GS} =0V, f=1MHz, T _j =25°C	-	1210	-	pF
Output Capacitance	C _{oss}		-	33.5	-	
Reverse Transfer Capacitance	C _{rss}		-	3.8	-	
Effective Output capacitance, Energy Related	C _{o(er)}	V _{DS} =0...325V, V _{GS} =0V, f=1MHz, T _j =25°C	-	50	-	
Effective Output Capacitance, Time Related	C _{o(tr)}		-	250	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =325V, I _D =15A, T _j =25°C	-	27.4	-	nC
Gate-Source Charge	Q _{gs}		-	7.9	-	
Gate-Drain Charge	Q _{gd}		-	12.2	-	
Reverse Recovery Charge	Q _{rr}	I _F =15A, di/dt=100A/μs, V _{GS} =0V, V _R =325V, T _j =25°C	-	4437	-	nC
Reverse Recovery Time	t _{rr}		-	323	-	ns
Peak Reverse Recovery Current	I _{rrm}		-	26	-	A
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =325V, I _D =15A, R _{GEN} =3Ω, T _j =25°C	-	39.4	-	ns
Turn-on Rise Time	t _r		-	32.5	-	
Turn-off Delay Time	t _{D(off)}		-	24	-	
Turn-off Fall Time	t _f		-	12.4	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of $150^\circ C$. The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



■ Typical Electrical and Thermal Characteristics Diagrams

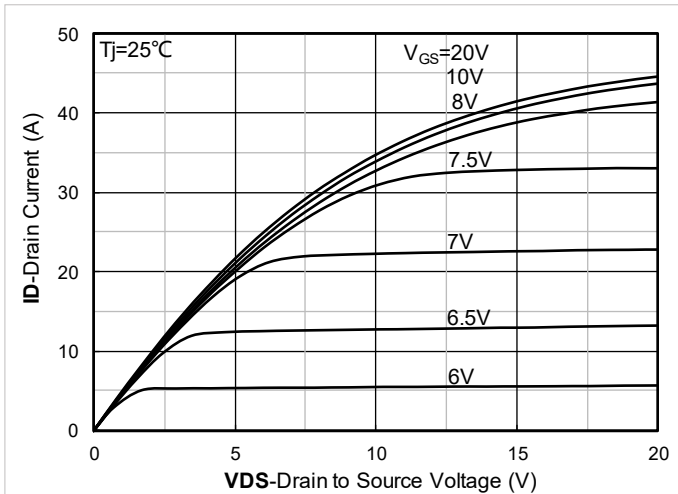


Figure 1. Output Characteristics; typical values

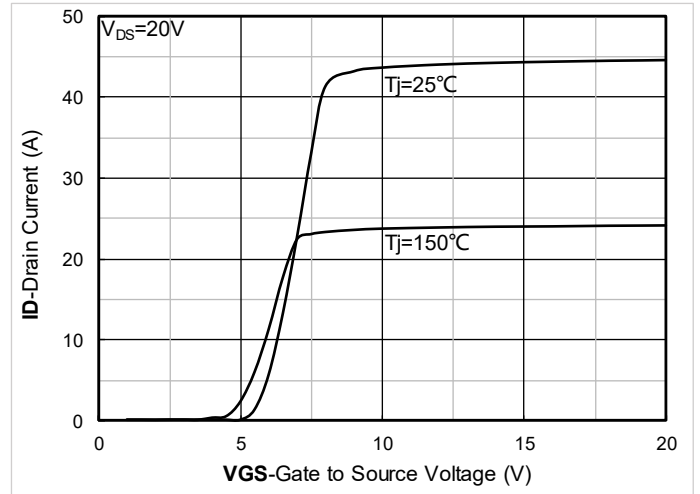


Figure 2. Transfer Characteristics; typical values

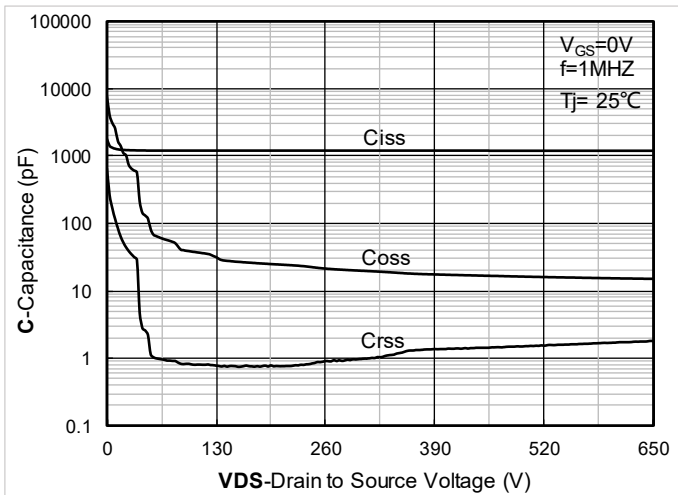


Figure 3. Capacitance Characteristics; typical values

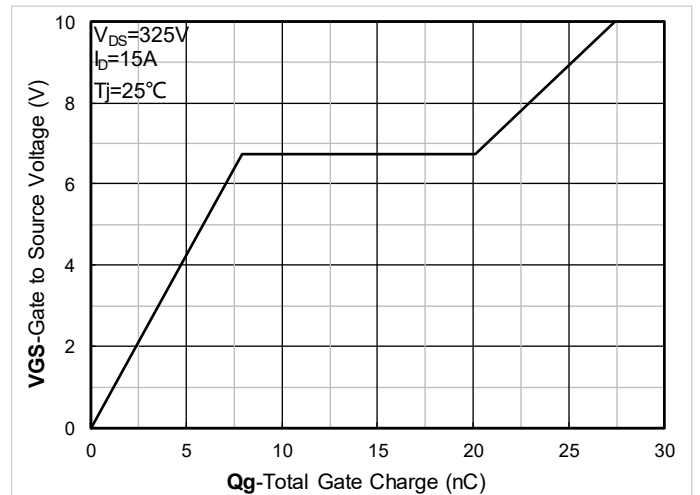


Figure 4. Gate Charge; typical values

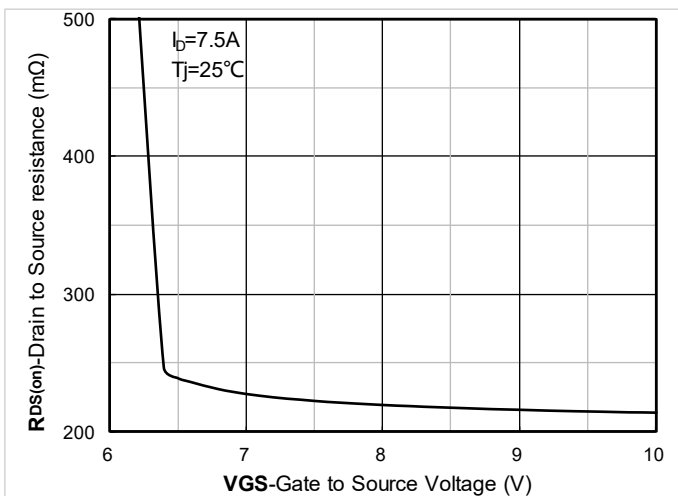


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

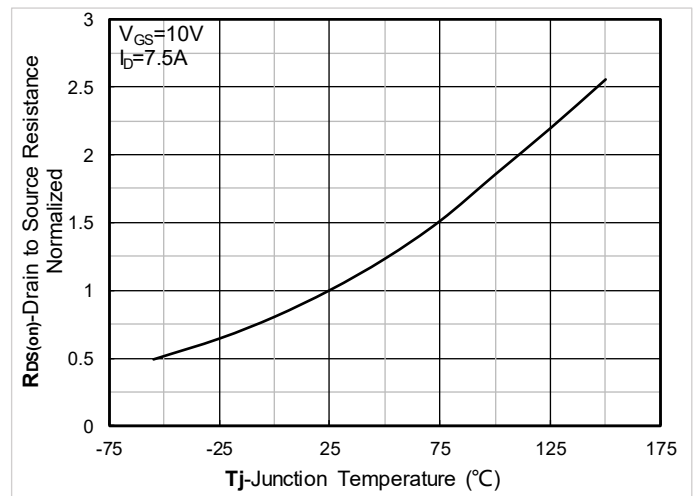


Figure 6. Normalized On-Resistance



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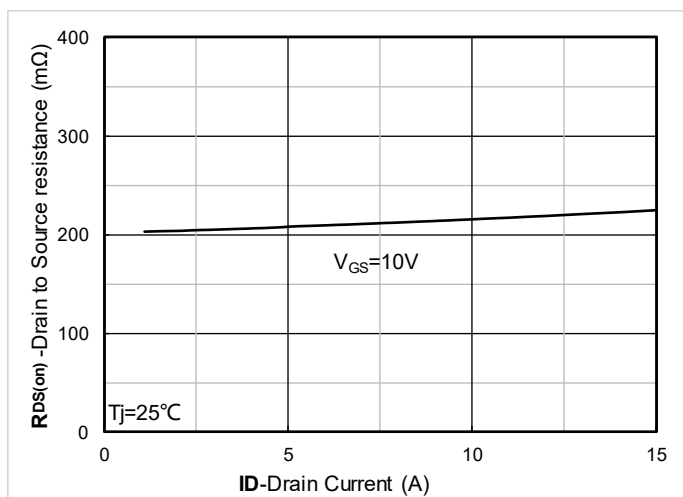


Figure 7. RDS(on) vs. Drain Current; typical values

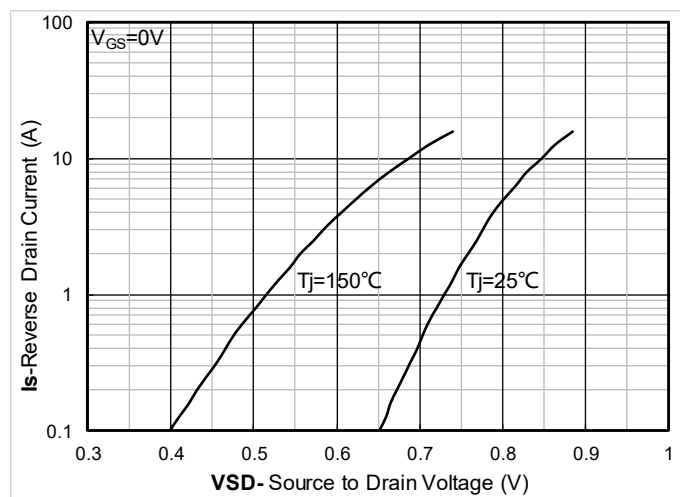


Figure 8. Forward characteristics of reverse diode; typical values

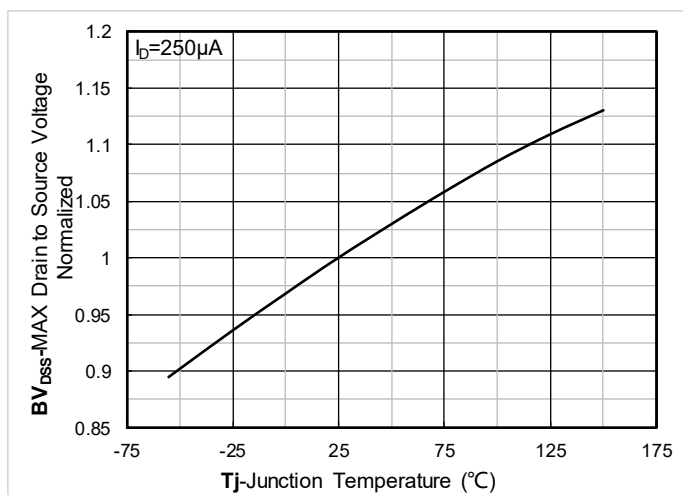


Figure 9. Normalized breakdown voltage

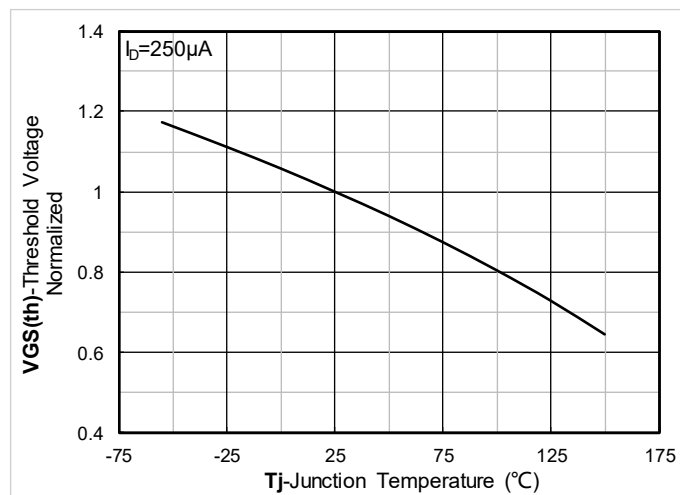


Figure 10. Normalized Threshold voltage

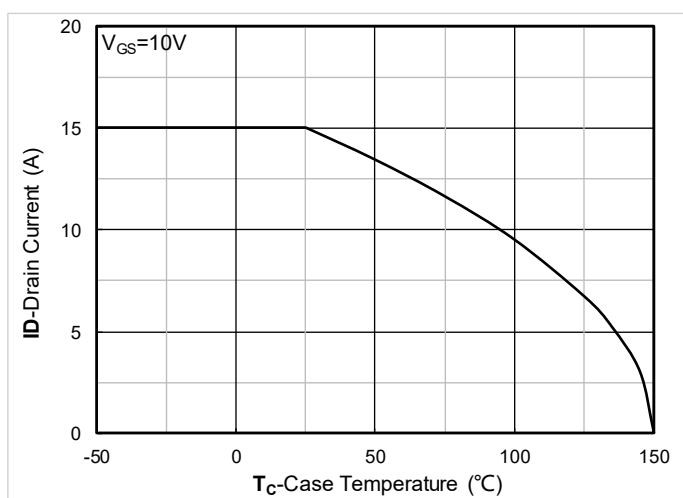


Figure 11. Current dissipation

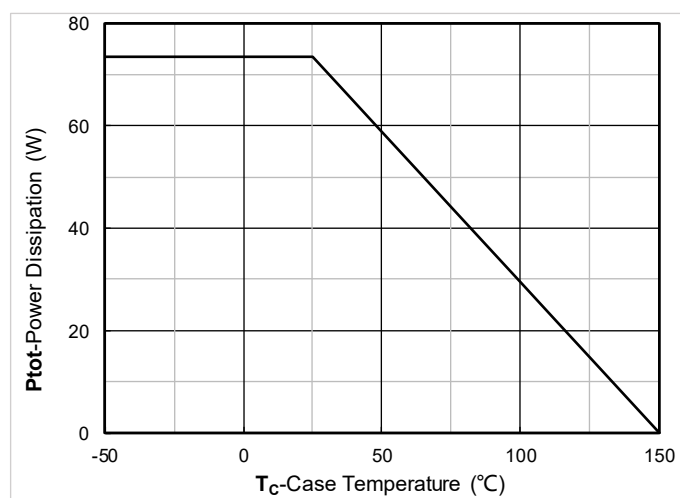


Figure 12. Power dissipation

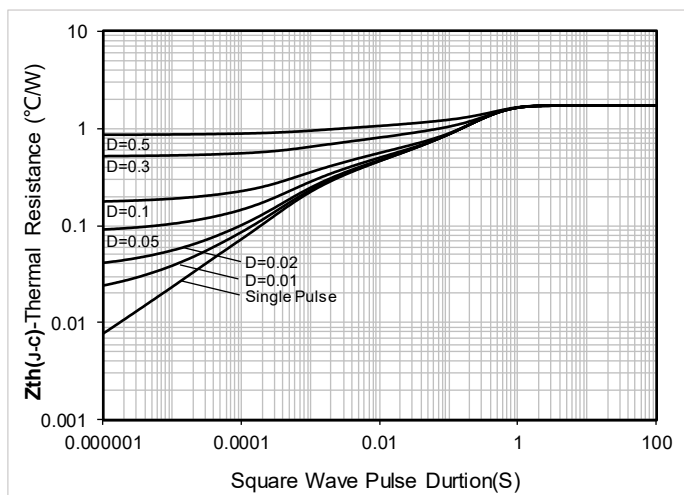


Figure 13. Maximum Transient Thermal Impedance

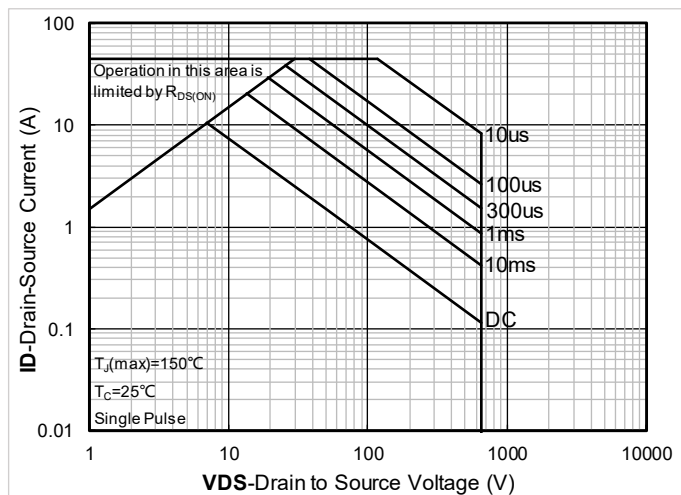


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

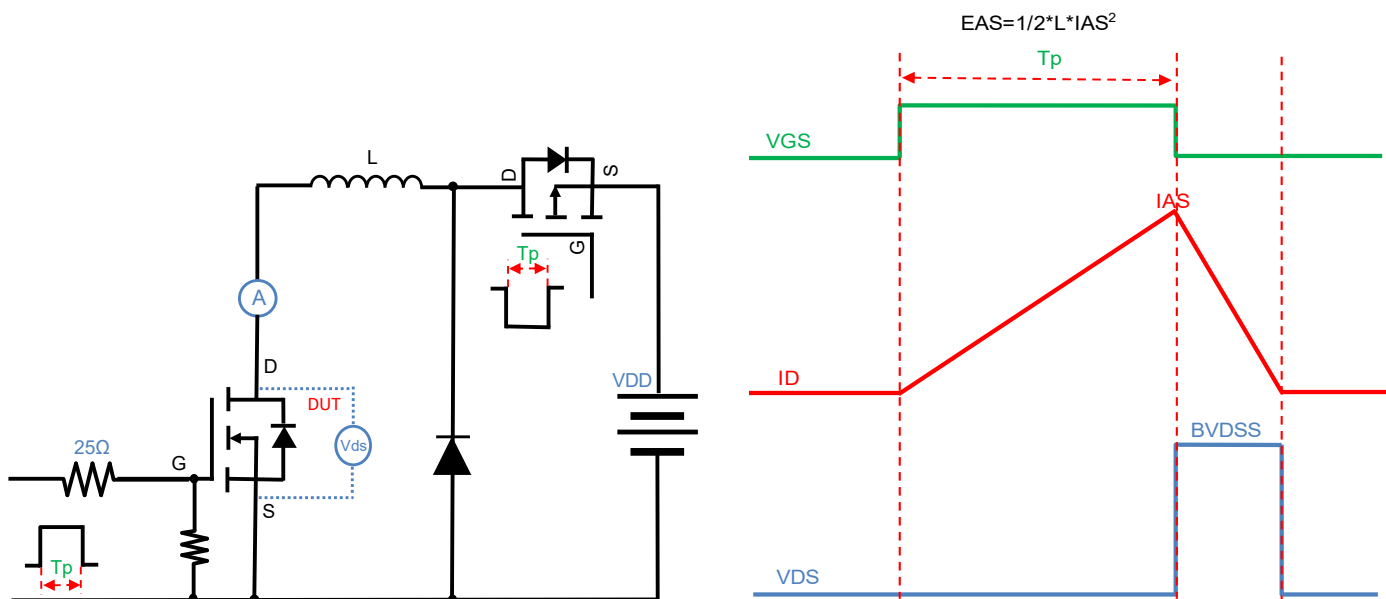


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

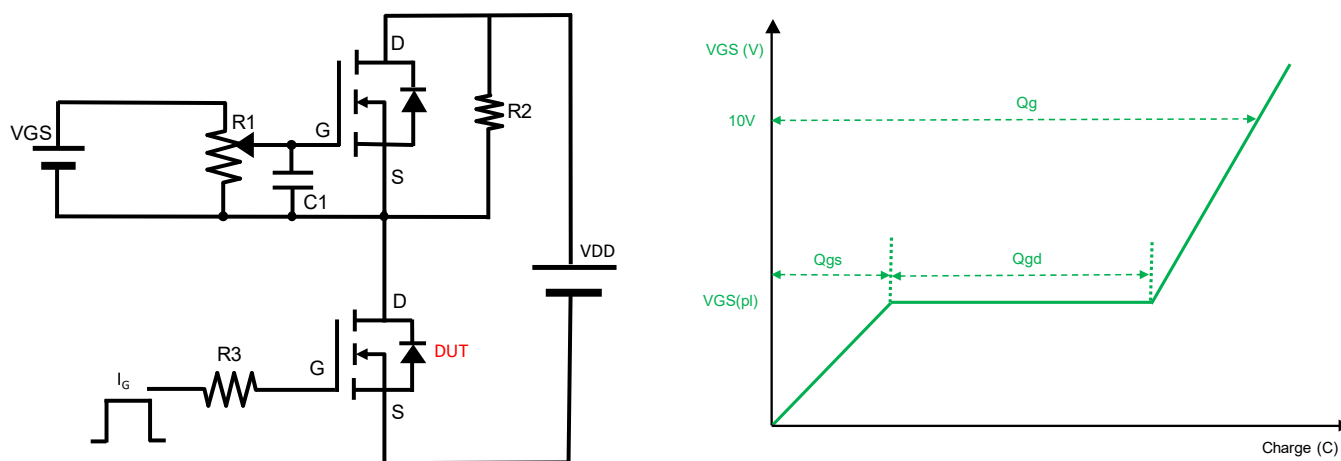


Figure B. Gate Charge Test Circuit & Waveform

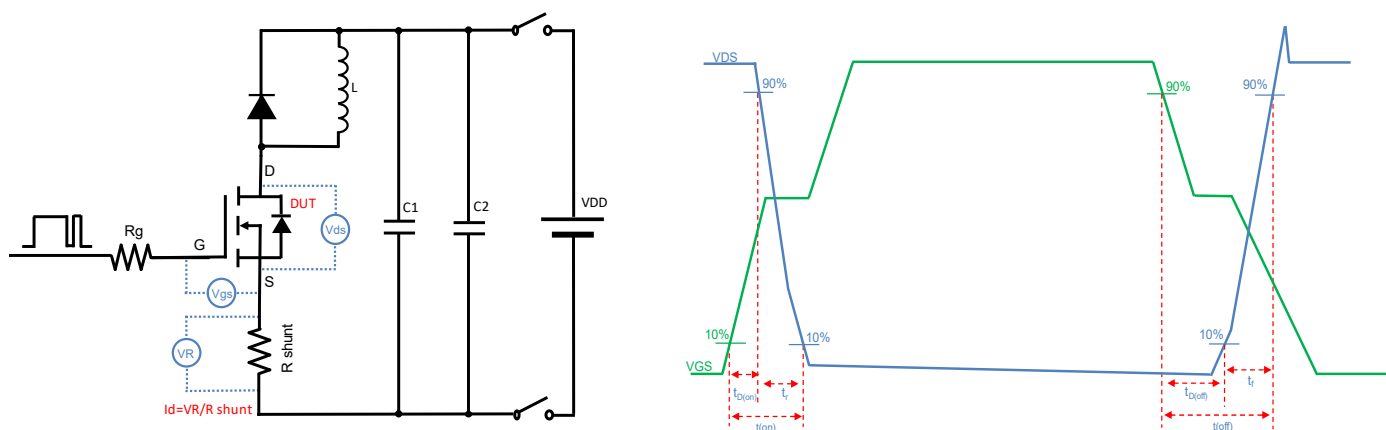


Figure C. Resistive Switching Test Circuit & Waveform

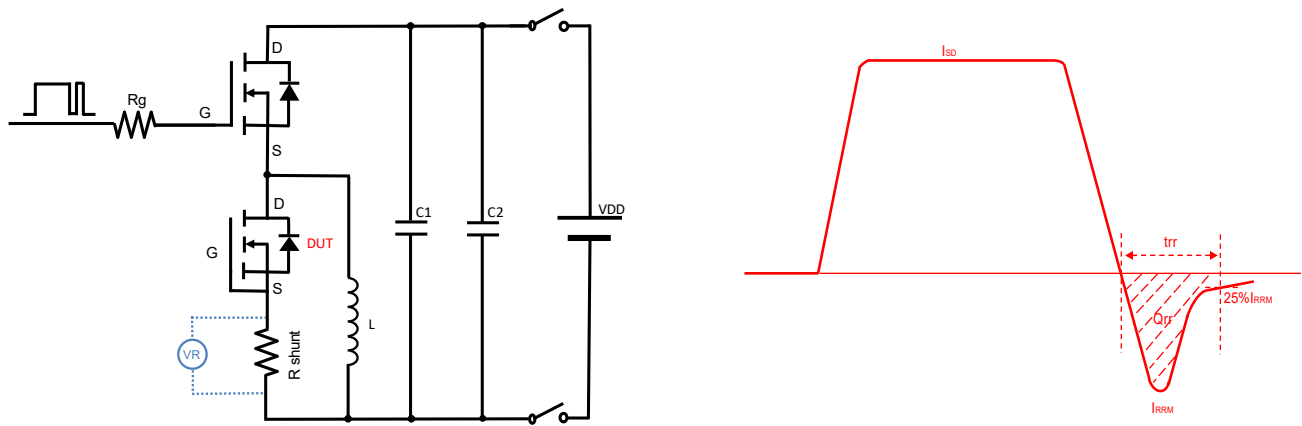
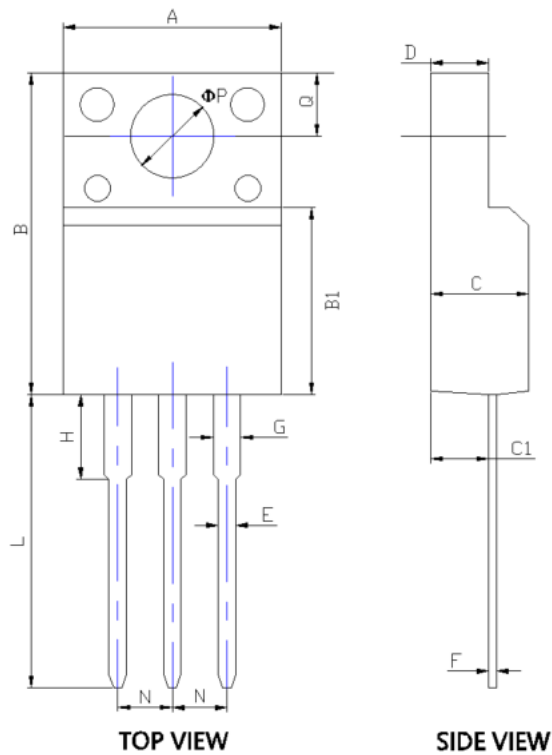


Figure D. Diode Recovery Test Circuit & Waveform



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■ ITO-220AB-E Package information



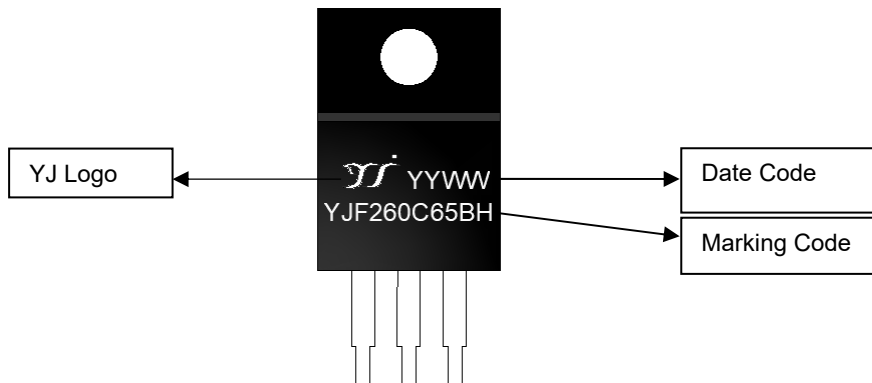
SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.390	0.406	9.900	10.300
B	0.610	0.633	15.500	16.100
B1	0.350	0.374	8.900	9.500
C	0.181	0.189	4.600	4.800
C1	0.087	0.110	2.200	2.800
D	0.096	0.104	2.450	2.650
E	0.028	0.035	0.700	0.900
F	0.016	0.024	0.400	0.600
G	0.044	0.056	1.120	1.420
H	0.134	0.150	3.400	3.800
L	0.496	0.512	12.600	13.000
N	0.100BSC.		2.540BSC.	
Q	0.126	0.142	3.200	3.600
ΦP	0.122	0.130	3.100	3.300

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJF260C65BH is marking code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



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